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Bipolar Transistor and MOSFET Device Models

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About the eBook

Continuous efforts to develop new semiconductor devices enable device manufacturers to make significant improvements in the information technology sector. Bipolar transistors and MOSFETS are two special electronic device components that are used to construct very large scale integrated (VLSI) circuits, allowing engineers to create powerful machines that are power efficient.

Contents

- ▶ Basics of Semiconductor Devices
- ▶ The pn Junction
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- ▶ The Short Channel MOSFET Model
- ▶ The Single-Gate SOI MOSFET Model
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